

3.3V~5V Input 24W Output Step-up DC/DC Converter

GENERAL DESCRIPTION

The XR2981 is a high frequency, high eff iciency DC to DC converter with an integrat ed 12A, $25m\Omega$ power switch capable of pro viding an output voltage up to 24V. The fix ed 600KHz allows the use of small external inductions and capacitors and provides fast transient response. It integrates Soft start, Comp,. Only need few components outsid e.

It can output 6V 3.5A, 9V 2A when 3.3V Battery input and output 6V 4.5A, 9V 3A w hen 3.6V Battery input at good heat dissipa tion condition.

FEATURES

- 2.7V to 5.5V input voltage Range
- Efficiency up to 96%

- 24V Boost converter with 12A switch current Limit
- 600KHz fixed Switching Frequency
- Integrated soft-start
- Thermal Shutdown
- Under voltage Lockout
- Support external LDO auxiliary power supply
- 8-Pin SOP-PP Package

APPLICATIONS

Portable Audio Amplifier Power Supply Power Bank QC 2.0/Type C Wireless Charger POS Printer Power Supply Small Motor Power Supply

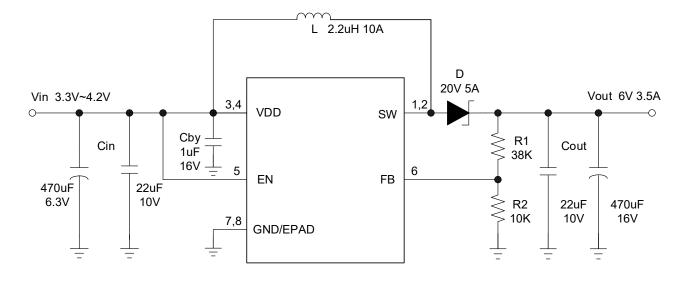


Figure 1. Typical Application Circuit1

(For Single Cell Li-Battery)



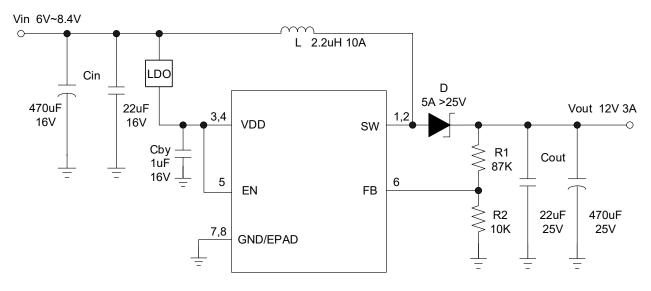


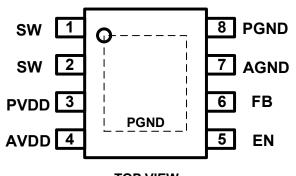
Figure 2 Typical Application Circuit2

(For Dual Cell Li-Battery)

ORDERING INFORMATION

PART NUMBER	TEMP RANGE	SWITCHING FREQUENCY	OUTPUT VOLTAGE(V)	ILIM(A)	PACKAGE
XR2981	-40°C~85°C	600KHZ	ADJ	12	SOP8-PP

PIN CONFIGURATION



TOP VIEW Figure 3. PIN Configuration

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PIN DESCRIPTION

XR2981 PIN NUMBER	PIN NAME	PIN DESCRIPTION			
1,2	SW	Switch pin			
3	PVDD	Input power supply pin, please connect to Cin as close as possible			
4	AVDD	Boost IC Logic power supply pin, if far from Cin, please add one 1uF MLCC as close as possible			
5	EN	Shutdown control input. Connect this pin to logic high level to enable the de vice			
6	FB	Feedback pin			
7	AGND	Analog ground			
8	PGND	Power ground			
EPAD	PGND	Please connect with PGND & AGND by mass metal for low Rdson, high efficiency and good heat dissipation			

ABSOLUTE MAXIMUM RATINGS

(NOTE: DO NOT EXCEED THESE LIMITS TO PREVENT DAMAGE TO THE DEVICE. EXPOSURE TO ABSOLUTE MAXIMUM RATING CONDITIONS FOR LONG PERIODS MAY AFFECT DEVICE RELIABIL-

PARAMETER	VALUE	UNIT
Supply Voltage VIN	-0.3 to 6.5	V
FB, EN Voltage	-0.3 to 6.5	V
SW Voltage	-0.3 to 26V	V
Operating Ambient Temperature	-40 to 85	°C
Maximum Junction Temperature	150	°C
Storage Temperature	-55 to 150	°C
Lead Temperature (Soldering, 10 sec)	300	°C



ELECTRICAL CHARACTERISTICS

Typical and limits appearing in normal type apply for V_{IN} =3.6V, TA = 25°C, unless otherwise specified.

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	ТҮР	MAX	UNIT
Input Voltage Range	V _{IN}		2.7		5.5	V
Boost output voltage range	V _{OUT}				24	V
UVLO Low Threshold	V _{UVLOL}			2.6		V
UVLO High Threshold	V _{UVLOH}			3.2		V
Operating Supply Current		V_{FB} =1.5V, EN=Vin, I _{Load} =0		140		μΑ
Shutdown Supply Current	I _{SUPPLY}	V _{EN} =0V, V _{IN} =3.6V			1	μΑ
Regulated Feedback Voltage	V_{FB}		1.21	1.24	1.27	V
Peak Inductor Current limit	I _{PEAK}			12		A
Oscillator Frequency	Fosc		400	600	800	KHz
Rds(ON) of N-channel FET		I _{SW} =1A		25		mΩ
Enable OFF Threshold		V _{EN} Falling			0.3	V
Enable ON Threshold		V _{EN} Rising	1.5			V
Enable Leakage Current			-0.1		0.1	μA
SW Leakage Current					1	μΑ



FUNCTIONAL BLOCK DIAGRAM

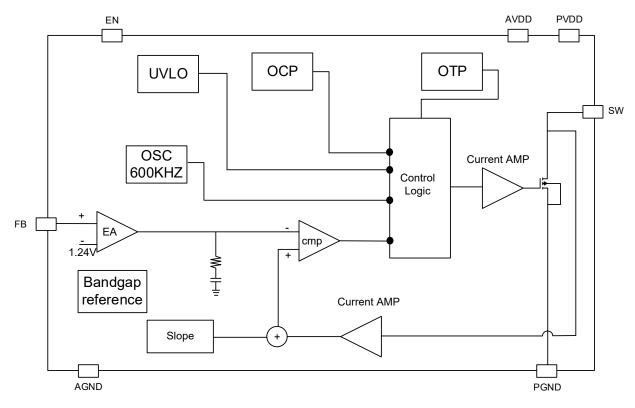


Figure 4. Functional Block Diagram

FUNCTIONAL DESCRIPTION

Normal operating mode

The boost converter is designed for outp ut voltage up to 24V with a 12A/24V power MOSFET. The low Rds(on) of the internal p ower switches enables better power efficien cy. The chip, which operates in a current m ode scheme with constant frequency 600K Hz. It operates with Pulse With Modulation (PWM). To avoid the inrush current during power up, soft start circuit is integrated in th e chip.

The controller circuit of the device is bas ed on a fixed frequency multiple feedback c ontroller topology. Input voltage, output volt age, and voltage drop on the NMOS switch are monitored and feedback to the regulato r. So changes in the operating conditions of the converter directly affect the duty cycle a nd must not take the indirect and slow way through the control loop and the error ampli fier. The control loop, determined by the err or amplifier, only has to handle small signal errors. The input for it is the feedback volta ge on the FB pin, the voltage on the interna I resistor divider. It is compared with the int ernal reference voltage to generate an accu rate and stable output voltage.

Cycle by cycle current limit

The peak current of the NMOS switch is also sensed to limit the maximum current fl owing through the switch and the inductor. The typical peak current limit is set to reach 12A.



Undervoltage lockout (UVLO)

Thermal shutdown

Under voltage lockout prevents operatio n of the device at input voltages below typi cal 2.6V when the input voltage is falling. When the input voltage is below the under voltage threshold, the device is shut down and the internal switch FETs are turned off. If the raised input voltage reaches under-v oltage lockout hysteresis(3.2V), the IC rest arts. A thermal shutdown is implemented to pr event damages due to excessive heat and power dissipation. Typically the thermal sh utdown threshold is 150°C. When the ther mal shutdown is triggered the device stops switching until the temperature falls below t ypically 136°C. Then the device starts switc hing again.

APPLICATION INFORMATION

INDUCTOR SELECTION

In normal operation, the inductor maintains continuous current to the output. The inductor current has a ripple that is dependent on the inductance value. The high inductance reduces the ripple current.

Selected inductor by actual application:

Manufac- turer	Part Number	Inductance (uH)	DRC max (mOhms)	Dimensions L*W*H(mm3)	ld	lsat
WURTH	74439358022	2.2	3.7	8.8*8.3*7.8	13A	30A
	74437368022	2.2	6.5	11*10*3.8	10A	28A
	7443330220	2.2	4.6	10.9*10*9.3	16.5A	22A
	74437349022	2.2	11.2	7.3*6.6*4.8	7.5A	14A
	744311220	2.2	11.4	6.9*7.0*3.8	9A	13A
ток	SPM6530T	2.2	17	7.1*6.5*3	8.4A	
	VLP6045LT	2.2	20	6*6*4.5	6.4A	

Table 1. Recommend Surface Mount Inductors

Notes: Please select inductor according to <u>Lin</u>. The IL need to be <u>1.5~2*I in</u>. For getting higher efficiency, need to use low DRC inductors.



INPUT CAPACITOR SELECTION

The input capacitor reduces input voltage ripple to the converter, low ESR ceramic cap acitor is highly recommended. For audio amplifier applications, A 22uF ceramic capacitor & 470uF E-cap is needed. low ESR tantalum capacitor is recommended for good ripple p erformance & dynamic response. The input capacitor should be placed as close as possib le to VIN and GND.

OUTPUT CAPACITOR SELECTION

A low ESR output capacitor is required in order to maintain low output voltage ripple. In the case of ceramic output capacitors, capacitor ESR is very small and does not contribut e to the ripple, so a lower capacitance value is acceptable when ceramic capacitors are u sed. For audio amplifier applications, A 22uF ceramic capacitor & 470uF E-cap is neede d. low ESR tantalum capacitor is recommended for good ripple performance & dynamic re sponse.

OUTPUT VOLTAGE PROGRAMMING

In the adjustable version, the output voltage is set by a resistive divider according to the following equation:

$$\mathbf{R}_1 = \mathbf{R}_2 \times \left(\frac{\mathbf{V}_{\mathsf{OUT}}}{1.24} - 1\right)$$

DIODE SELECTION

According to max lout and max Vout, you can select suitable diode.

Normally we select diode If=(1.5~2)*loutmax and VR=(1.5~2)*Voutmax. For high efficiency, suggest that you select low Vf Schottky diode.

For example, 3.3V~4.2Vin 6V 3.5Aout, you can select SS12P31.

For common application, you can select SS34 or SS54 according to loutmax

LDO Selection

For Typical Application Circuit2, you need to select LDO--Input voltage range 4V~15V(o r higher). Iout>=100mA. Output voltage is preferred to set 4.2V~4.5V.

LDO need enough input & output capacity, please select suitable external parts and lay out them according to LDO's datasheet.



LAYOUT CONSIDERATIONS

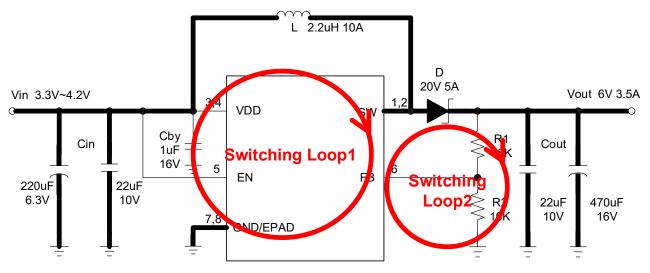
1. The input capacitor, output capacitor, and the inductor should be placed as close as p ossible to the IC to keep resistance very low and the switching loop very small for EMI per formance.

2. The FB pin connection should be made as close to the load as possible so that the v oltage at the load is the expected regulated value. And place FB network far from Switchi ng node.

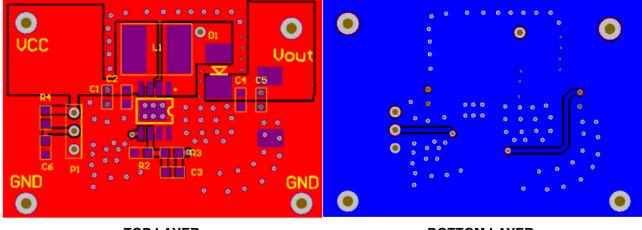
3.Please make sure that the big current circuits are board and short to reduce the circuit t Rds(on), all ground connection must be tied together. Use a broad ground plane to establish the lowest resistance possible between all connections to achieve the best thermal and noise performance.

4. The switch node connection should be low resistance to reduce power losses.

5. The heavy copper board in big current output is recommended for high efficiency and good heat dissipation.



PCB LAYOUT GUIDE



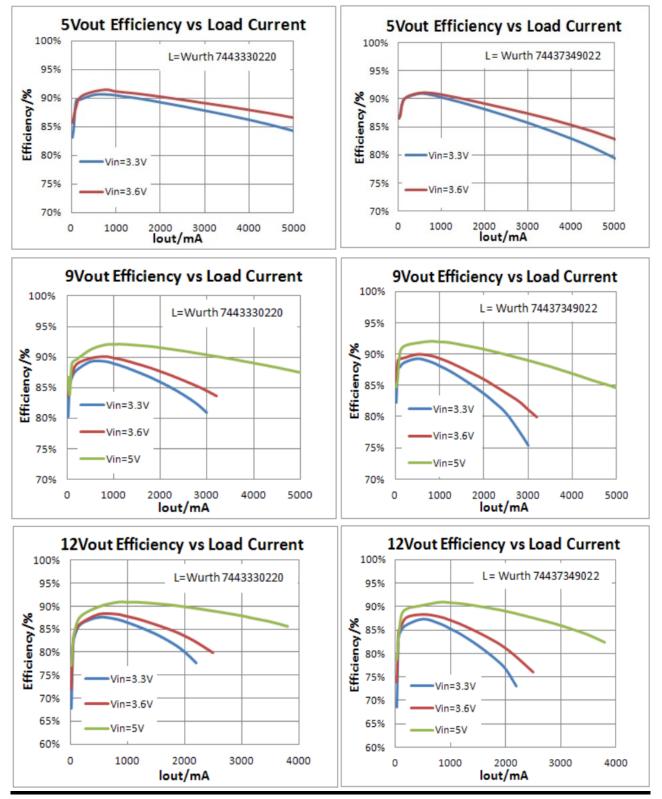
TOP LAYER

BOTTOM LAYER

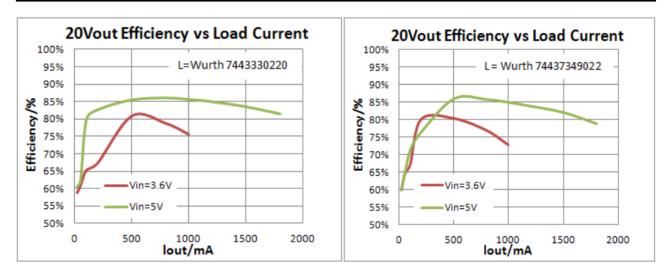


TYPICAL PERFORMANCE CHARACTERISTICS

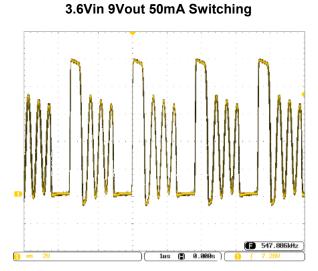
L=2.2uH-Wurth, Cin or Cout=22uF, MLCC+220uF Ecap, D=SS12P31, if not mentioned





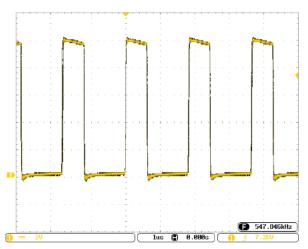


Note: Efficiency data is based on demo test at 20°C. If work at big current for long time, maybe thermal shutdown. its load capacity is related with heat dissipation conditions.

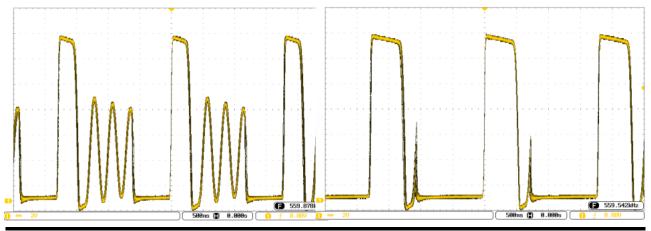


3.6Vin 12Vout 50mA Switching

3.6Vin 9Vout 1A Switching



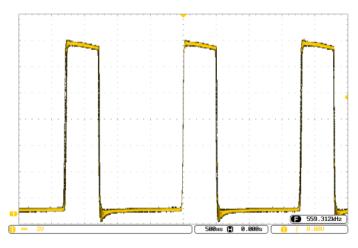
3.6Vin 12Vout 200mA Switching



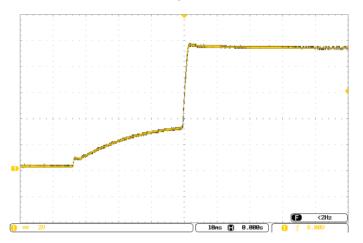
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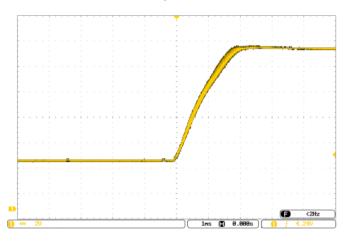
3.6Vin 12Vout 1A Switching



9Vout Startup from Vin

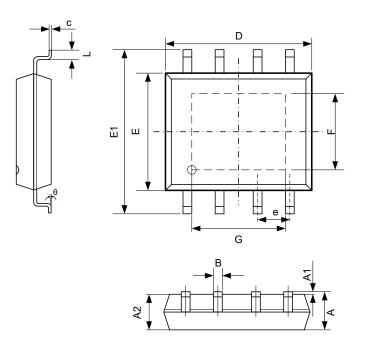


9Vout Startup from EN





PACKAGE OUTLINE(SOP8-PP)



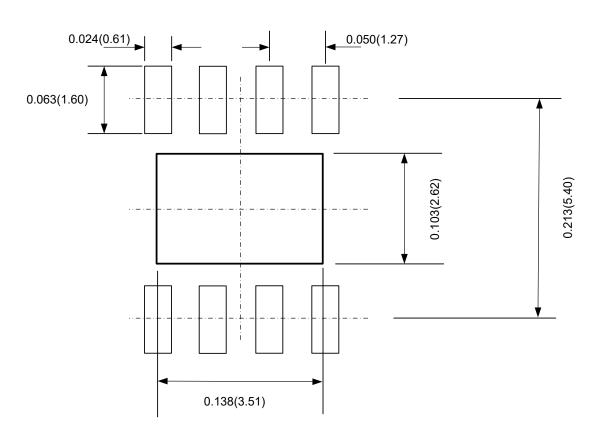
Symbol	Dimensions Ir	n Millimetres	Dimensions In Inches		
	Min	Max	Min	Мах	
A	1.30	1.75	0.051	0.069	
A1	0.000	0.250	0.000	0.010	
A2	1.350	1.550	0.053	0.061	
В	0.330	0.510	0.013	0.020	
С	0.170	0.250	0.007	0.010	
D	4.700	5.100	0.185	0.201	
E	3.800	4.000	0.150	0.157	
E1	5.800	6.300	0.228	0.248	
е	1.27TYP		0.050TYP		
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	
F	2.26	2.56	0.089	0.101	
G	3.15	3.45	0.124	0.136	

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PACKAGE OUTLINE(SOP8-PP)

In order to increase the driver current capability of XR2981 and improve the temperature of package, Please ensure Epad and enough ground PCB to release energy.





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